UNITED STATES PATENT AND TRADEMARK OFFICE

CERTIFICATE OF CORRECTION

PATENT NO. : 7,749,860 B2
APPLICATION NO. : 09/392034
DATED : July 6, 2010
INVENTOR(S) : Fernando Gonzalez, David Chapek and Ranshir P. S. Thakur

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the title page:
In Item (54), change "**METHOD FOR FORMING A SELF-ALIGNED T-SHAPED ISOLATION TRENCH**" to **--METHOD FOR FORMING A SELF-ALIGNED ISOLATION TRENCH--**

In the specification:
COLUMN 1, LINE 2, delete "**T-SHAPED**"

In the claims:

CLAIM 1,	COLUMN 10,	LINE 59,	after "forming" insert --a first dielectric material upon-- and change "layer upon" to --over--
CLAIM 1,	COLUMN 10,	LINE 60,	delete "forming a first dielectric layer upon the oxide layer;"
CLAIM 1,	COLUMN 10,	LINE 61,	change "layer" to --material-- and after "expose" insert --a plurality of areas of--
CLAIM 1,	COLUMN 10,	LINE 62,	after "oxide" delete "layer at a plurality of areas"
CLAIM 1,	COLUMN 10,	LINE 63,	change "layer over the oxide layer and" to --material over--
CLAIM 1,	COLUMN 10,	LINES 64-66,	after "the first dielectric" delete "layer, wherein the forming a second dielectric layer includes forming a second dielectric layer over" and insert --material-- therefor
CLAIM 1,	COLUMN 10,	LINE 66,	after "with the" insert --plurality of--, after "exposed" insert --areas of the-- and after "oxide" delete "layer at"
CLAIM 1,	COLUMN 10,	LINE 67,	delete "the plurality of areas"
CLAIM 1,	COLUMN 11,	LINE 1,	change "layer" to --material--
CLAIM 1,	COLUMN 11,	LINE 2,	change "from the second dielectric layer," to --at peripheral edges of the plurality of exposed areas of--
CLAIM 1,	COLUMN 11,	LINE 3,	delete "wherein each spacer is situated upon" and delete "layer, is"

Signed and Sealed this

Sixteenth Day of November, 2010

David J. Kappos

David J. Kappos
Director of the United States Patent and Trademark Office

In the claims (continued):

CLAIM 1,	COLUMN 11,	LINES 4-5,	after "contact with" insert --lateral edges of-- and delete "layer, and is adjacent to an area of the plurality of areas" and insert --material-- therefor
CLAIM 1,	COLUMN 11,	LINES 6-11,	change "forming a plurality of isolation trenches extending below the oxide layer into the semiconductor substrate, wherein each isolation trench is adjacent to and below a pair of the spacers and is situated at a corresponding area of the plurality of areas, and wherein each isolation trench has a top edge;" to --removing a portion of material from the plurality of areas of the oxide at locations between adjacent portions of the plurality of spacers to form a plurality of isolation trenches extending into the semiconductor substrate;--
CLAIM 1,	COLUMN 11,	LINE 12,	change "trench;" to --trench of the plurality of isolation trenches;--
CLAIM 1,	COLUMN 11,	LINE 13,	delete "filling each isolation trench with" and insert therefor --implanting ions in the plurality of isolation trenches in a direction substantially orthogonal to a plane of the oxide;--, then insert --depositing-- before "a conformal," and change "layer" to --material in each isolation trench,--
CLAIM 1,	COLUMN 11,	LINE 14,	change "conformal layer" to --conformal material-- and change "above the oxide layer" to --over remaining portions of the oxide--
CLAIM 1,	COLUMN 11,	LINE 16,	change "filling" to --depositing-- and after "performed" delete "by depositing the conformal layer,"
CLAIM 1,	COLUMN 11,	LINE 17,	delete "and the depositing is carried out"
CLAIM 1,	COLUMN 11,	LINE 19,	change "layer" to --material--
CLAIM 1,	COLUMN 11,	LINE 20,	change "layer;" to --material;--
CLAIM 1,	COLUMN 11,	LINES 21-23,	change "substantially simultaneously subjecting the entire upper surface contour of" to --removing portions of--, change "layer to a planarizing process and" to --material overlying the remaining portions of the oxide by--, and change "layer" to --material--
CLAIM 1,	COLUMN 11,	LINES 24-25,	change "layer" to --material--, change "to form therefrom" to --such that--, and change "that is" to --is--
CLAIM 1,	COLUMN 11,	LINES 26-28,	change "surfaces; and" to --surfaces,--, delete the paragraph break, delete "fusing the oxide layer, liner, spacers, and conformal layer; wherein," and change "layer comprises" to --material comprising--

In the claims (continued):

CLAIM 1,	COLUMN 11,	LINE 30,	change "trenches." to --trenches; and--, insert a paragraph break and then insert --removing the first dielectric material and portions of the oxide underlying the first dielectric material such that the conformal material fills each said isolation trench, extends horizontally away from each said isolation trench upon remaining portions of the oxide and sidewalls of the conformal material start on an upper surface of the semiconductor substrate and are substantially orthogonal to the upper surface contour of the conformal material.--
CLAIM 4,	COLUMN 11,	LINE 37,	change "further comprising" to --wherein implanting ions in the plurality of isolation trenches in a direction substantially orthogonal to a plane of the oxide comprises--
CLAIM 4,	COLUMN 11,	LINE 38,	after "each" insert --of said plurality of--
CLAIM 4,	COLUMN 11,	LINE 39,	change "trench" to --trenches--
CLAIM 4,	COLUMN 11,	LINES 40-41,	change "the upper surface for each isolation trench is formed" to --removing portions of the conformal material overlying the remaining portions of the oxide comprises removing portions of the conformal material overlying the remaining portions of the oxide--
CLAIM 6,	COLUMN 11,	LINE 45,	change "dielectric layer" to --dielectric material-- and change "oxide layer" to --oxide--
CLAIM 6,	COLUMN 11,	LINE 47,	change "dielectric layer" to --dielectric material-- and after "expose" insert --a plurality of areas of--
CLAIM 6,	COLUMN 11,	LINE 48,	after "oxide" delete "layer at a plurality of areas"
CLAIM 6,	COLUMN 11,	LINE 49,	change "dielectric layer" to --dielectric material-- and after "over" delete "the oxide layer and"
CLAIM 6,	COLUMN 11,	LINES 50-53,	change "layer, wherein the forming a second dielectric layer includes forming a second dielectric layer on" to --material--, change "exposed oxide layer at the plurality of" to --plurality of exposed-- and after "areas" insert --of the oxide--
CLAIM 6,	COLUMN 11,	LINE 54,	change "dielectric layer" to --dielectric material--
CLAIM 6,	COLUMN 11,	LINE 55,	change "from the second dielectric layer," to --at peripheral edges of the plurality of exposed areas of--
CLAIM 6,	COLUMN 11,	LINE 56,	delete "wherein each spacer is situated upon" and delete "layer, is"
CLAIM 6,	COLUMN 11,	LINES 57-58,	after "with" insert --lateral edges of-- and change "layer, and is adjacent to an area of the plurality of areas;" to --material;--
CLAIM 6,	COLUMN 11,	LINE 60,	change "forming" to --removing a portion of material from the plurality of areas of the oxide at locations between adjacent portions of the plurality of spacers to form-- and delete "below"
CLAIM 6,	COLUMN 11,	LINE 61,	delete "the oxide layer" and change "substrate," to --substrate;--

In the claims (continued):

CLAIM 6,	COLUMN 11,	LINES 62-65,	delete "wherein each isolation trench is adjacent to and below a pair of the spacers and is situated at a corresponding area of the plurality of areas, and wherein each isolation trench has an edge;"
CLAIM 6,	COLUMN 12,	LINE 1,	change "filling each isolation trench with" to --implanting ions in the plurality of isolation trenches in a direction substantially orthogonal to a plane of the oxide;--, then insert a paragraph break, insert --depositing-- before "a conformal" and change "layer," to --material filling each isolation trench,--
CLAIM 6,	COLUMN 12,	LINE 2,	change "layer" to --material--, change "above" to --over remaining portions of--, and after "oxide" delete "layer"
CLAIM 6,	COLUMN 12,	LINE 4,	change "filling is performed by" to --the-- and delete "the conformal layer"
CLAIM 6,	COLUMN 12,	LINE 5,	delete "and depositing"
CLAIM 6,	COLUMN 12,	LINE 7,	change "layer" to --material--
CLAIM 6,	COLUMN 12,	LINE 8,	change "layer;" to --material;--
CLAIM 6,	COLUMN 12,	LINES 9-10,	change "substantially simultaneously subjecting an entire upper surface contour" to --removing portions-- and change "layer to a" to --material that overlie the remaining portions of the oxide by--
CLAIM 6,	COLUMN 12,	LINE 11,	delete "process and planarizing" and change "layer" to --material--
CLAIM 6,	COLUMN 12,	LINE 12,	delete "therefrom"
CLAIM 6,	COLUMN 12,	LINE 14,	delete "fusing the oxide layer, spacers and conformal layer;"
CLAIM 6,	COLUMN 12,	LINE 15,	before "wherein" insert --removing the first dielectric material and portions of the oxide underlying the first dielectric material such that the conformal material fills each isolation trench, extends horizontally away from each isolation trench upon remaining portions of the oxide and sidewalls of the conformal material begin on an upper surface of the semiconductor substrate and are oriented substantially orthogonal to the upper surface contour of the conformal material--
CLAIM 6,	COLUMN 12,	LINE 16,	change "layer comprises a material that" to --material--
CLAIM 6,	COLUMN 12,	LINE 19,	change "layer" to --material--
CLAIM 6,	COLUMN 12,	LINE 21,	change "layer" to --material--
CLAIM 6,	COLUMN 12,	LINE 22,	change "oxide layer; and" to --oxide; and--
CLAIM 6,	COLUMN 12,	LINE 23,	change "layer" to --material--
CLAIM 6,	COLUMN 12,	LINE 24,	change "oxide layer." to --oxide.--
CLAIM 9,	COLUMN 12,	LINE 36,	change "material the ratio is" to --material using an etch recipe that etches the conformal material faster than the first dielectric material by a ratio-- and change "from about" to --of from about--
CLAIM 10,	COLUMN 12,	LINE 38,	change "overlying" to --that overlie--

In the claims (continued):

CLAIM 13,	COLUMN 12,	LINE 61,	change "oxide layer" to --oxide--
CLAIM 13,	COLUMN 12,	LINE 62,	change "nitride layer" to --nitride-- and change "oxide layer;" to --oxide;--
CLAIM 13,	COLUMN 12,	LINE 63,	change "nitride layer" to --nitride-- and after "expose" insert --a plurality of areas of--
CLAIM 13,	COLUMN 12,	LINE 64,	change "oxide layer at a plurality of areas;" to --oxide;--
CLAIM 13,	COLUMN 12,	LINE 65,	change "layer over the oxide layer" to --material over--
CLAIM 13,	COLUMN 12,	LINE 66,	delete "and over," and delete "layer, wherein forming a first"
CLAIM 13,	COLUMN 12,	LINE 67,	delete "silicon dioxide layer includes forming a first silicon"
CLAIM 13,	COLUMN 13,	LINE 1,	delete "dioxide layer on" and change "the exposed oxide" to --the plurality of exposed areas of the oxide;--
CLAIM 13,	COLUMN 13,	LINE 2,	delete "layer at the plurality of areas;"
CLAIM 13,	COLUMN 13,	LINE 3,	change "layer" to --material--
CLAIM 13,	COLUMN 13,	LINE 4,	change "from the first silicon dioxide layer," to --at the peripheral edges of the plurality of exposed areas of--
CLAIM 13,	COLUMN 13,	LINE 5,	delete "wherein each spacer is situated upon" and delete "layer, is"
CLAIM 13,	COLUMN 13,	LINES 6-7,	change "silicon nitride layer, and is adjacent to an area of the plurality of areas;" to --lateral edges of the silicon nitride;--
CLAIM 13,	COLUMN 13,	LINE 8,	change "forming" to --removing a portion of material from the plurality of areas at locations between adjacent portions of the plurality of spacers to form-- and change "below" to --into --
CLAIM 13,	COLUMN 13,	LINE 9,	delete "the oxide layer into and terminating within"
CLAIM 13,	COLUMN 13,	LINES 10-13,	change "substrate, wherein each isolation trench is adjacent to and below a pair of the spacers and is situated at a corresponding area of the plurality of areas, and wherein each isolation trench has a top edge;" to --substrate;--
CLAIM 13,	COLUMN 13,	LINES 17-21,	change "trench, the liner being confined preferentially within each isolation trench and extending from an interface thereof with the oxide layer to the termination of the isolation trench within the semiconductor substrate;" to --trench;--
CLAIM 13,	COLUMN 13,	LINE 22,	change "filling each isolation trench with" to --implanting ions in the plurality of isolation trenches in a direction substantially orthogonal to a plane of the oxide;--, insert a paragraph break, and then insert --depositing--
CLAIM 13,	COLUMN 13,	LINE 23,	change "layer, the conformal second silicon dioxide" to --material filling--
CLAIM 13,	COLUMN 13,	LINE 24,	delete "layer within" and change "trench extending above" to --trench, the conformal second silicon dioxide material within each isolation trench and extending over remaining portions of--

In the claims (continued):

CLAIM 13,	COLUMN 13, LINE 25,	delete "layer"
CLAIM 13,	COLUMN 13, LINE 26,	change "wherein filling is performed by depositing the" to --the--
CLAIM 13,	COLUMN 13, LINE 27,	delete "conformal second silicon dioxide layer, and"
CLAIM 13,	COLUMN 13, LINE 30,	delete "layer"
CLAIM 13,	COLUMN 13, LINE 31,	change "dioxide layer;" to --dioxide material;--
CLAIM 13,	COLUMN 13, LINE 32,	delete "substantially simultaneously subjecting an entire upper"
CLAIM 13,	COLUMN 13, LINE 33,	change "surface contour" to --removing portions--
CLAIM 13,	COLUMN 13, LINE 34,	change "layer to a" to --material by-- and delete "process so as to remove"
CLAIM 13,	COLUMN 13, LINE 35,	change "dioxide layer" to --dioxide material--
CLAIM 13,	COLUMN 13, LINE 37,	change "surfaces and being situated" to --surfaces,--
CLAIM 13,	COLUMN 13, LINE 38,	delete "above the oxide layer," and change "a material that is" to --an--
CLAIM 13,	COLUMN 13, LINE 39,	after "insulative" insert --material--
CLAIM 13,	COLUMN 13, LINES 41-42,	change "fusing the oxide layer, liner, spacers, and conformal second silicon dioxide layer." to --removing the silicon nitride and portions of the oxide underlying the silicon nitride such that the conformal second silicon dioxide material fills each isolation trench, extends horizontally away from each isolation trench upon remaining portions of the oxide and sidewalls of the second silicon dioxide material start on an upper surface of the semiconductor substrate and lie substantially orthogonal to the upper surface contour of the second silicon dioxide material.--
CLAIM 17,	COLUMN 13, LINE 54,	change "oxide layer" to --oxide--
CLAIM 17,	COLUMN 13, LINE 55,	change "a polysilicon layer" to --polysilicon-- and change "oxide layer;" to --oxide;--
CLAIM 17,	COLUMN 13, LINE 56,	change "dielectric layer" to --dielectric material-- and change "polysilicon layer;" to --polysilicon;--
CLAIM 17,	COLUMN 13, LINE 57,	change "dielectric layer" to --dielectric material--
CLAIM 17,	COLUMN 13, LINES 58-59,	change "layer to expose" to --to expose-- and after "expose" insert --a plurality of areas of-- and change "oxide layer at a plurality of areas:" to --oxide:--
CLAIM 17,	COLUMN 13, LINE 60,	change "dielectric layer" to --dielectric material--
CLAIM 17,	COLUMN 13, LINE 61,	change "oxide layer, the polysilicon layer, and" to --polysilicon,--
CLAIM 17,	COLUMN 13, LINES 62-65,	change "layer, wherein the forming a second dielectric layer includes forming a second dielectric layer on and in contact with the exposed oxide layer at the plurality of areas;" to --material and in contact with the plurality of exposed areas of the oxide;--
CLAIM 17,	COLUMN 13, LINE 66,	change "dielectric layer" to --dielectric material--

In the claims (continued):

CLAIM 17,	COLUMN 13,	LINE 67,	change "from the second dielectric layer," to --at peripheral edges of the plurality of exposed areas of the oxide--
CLAIM 17,	COLUMN 14,	LINE 1,	delete "wherein each spacer is upon the oxide layer, is"
CLAIM 17,	COLUMN 14,	LINE 2,	change "both the polysilicon layer and" to --lateral edges of--
CLAIM 17,	COLUMN 14,	LINE 3,	change "layer, and is adjacent to an area of the plurality of areas;" to --material;--
CLAIM 17,	COLUMN 14,	LINE 4,	change "forming" to --removing a portion of material from the plurality of areas of the oxide at locations between adjacent portions of the plurality of spacers to form-- and delete "below"
CLAIM 17,	COLUMN 14,	LINE 5,	delete "the oxide layer and from top edges"
CLAIM 17,	COLUMN 14,	LINES 6-9,	change "substrate, wherein each isolation trench is adjacent to and below a pair of the spacers and is situated at a corresponding area of the plurality of areas;" to --substrate;--
CLAIM 17,	COLUMN 14,	LINE 11,	before "filling" insert --implanting ions in the plurality of isolation trenches in a direction substantially orthogonal to a plane of the oxide;--, insert a paragraph break, insert --depositing a conformal third material--, and delete "with a conformal third layer,"
CLAIM 17,	COLUMN 14,	LINE 12,	change "layer extending above" to --material extending over remaining portions of--
CLAIM 17,	COLUMN 14,	LINE 13,	delete "layer"
CLAIM 17,	COLUMN 14,	LINE 14,	delete "filling is performed by depositing the conformal"
CLAIM 17,	COLUMN 14,	LINE 15,	delete "third layer, and"
CLAIM 17,	COLUMN 14,	LINE 17,	change "dielectric layer" to --dielectric material--
CLAIM 17,	COLUMN 14,	LINE 18,	change "third layer;" to --third material;--
CLAIM 17,	COLUMN 14,	LINES 19-20,	change "substantially simultaneously subjecting an entire upper surface contour" to --removing portions-- and change "layer to a" to --material by--
CLAIM 17,	COLUMN 14,	LINE 21,	delete "process and planarizing"
CLAIM 17,	COLUMN 14,	LINE 22,	change "layer" to --material-- and delete "therefrom"
CLAIM 17,	COLUMN 14,	LINE 25,	change "fusing the oxide layer, spacers and conformal third layer;" to --removing the first dielectric material, polysilicon and portions of the oxide underlying the first dielectric material such that the conformal third material fills each isolation trench, extends horizontally away from each isolation trench upon remaining portions of the oxide and sidewalls of the conformal third material extend from an upper surface of the semiconductor substrate to the upper surface contour of the conformal third material and the sidewalls are substantially orthogonal to the upper surface contour of the conformal third material;--

In the claims (continued):

CLAIM 17,	COLUMN 14,	LINE 30,	change "third layer," to --third material,--
CLAIM 18,	COLUMN 14,	LINES 32-33,	change "the upper surface for each isolation trench is formed" to --removing portions of the conformal third material comprises removing portions of the conformal third material--
CLAIM 22,	COLUMN 14,	LINE 52,	change "oxide layer" to --oxide--
CLAIM 22,	COLUMN 14,	LINE 53,	change "a polysilicon layer" to --polysilicon-- and change "oxide layer;" to --oxide;--
CLAIM 22,	COLUMN 14,	LINE 54,	change "dielectric layer" to --dielectric material-- and change "polysilicon layer;" to --polysilicon;--
CLAIM 22,	COLUMN 14,	LINES 55-57,	change "dielectric layer" to --dielectric material--, change "polysilicon layer" to --polysilicon--, and change "expose the oxide layer at a plurality of areas;" to --expose a plurality of areas of the oxide;--
CLAIM 22,	COLUMN 14,	LINE 58,	change "dielectric layer conformally" to --dielectric material--
CLAIM 22,	COLUMN 14,	LINE 59,	delete "oxide layer, the" and change "polysilicon layer, and" to --polysilicon,--
CLAIM 22,	COLUMN 14,	LINES 60-62,	change "layer, wherein forming a second dielectric layer includes forming a second dielectric layer on and in contact with the exposed oxide layer at the plurality of areas;" to --material and in contact with the plurality of exposed areas of the oxide;--
CLAIM 22,	COLUMN 14,	LINE 63,	change "dielectric layer" to --dielectric material--
CLAIM 22,	COLUMN 14,	LINE 64,	change "from the second dielectric layer," to --at the peripheral edges of the plurality of exposed areas of--
CLAIM 22,	COLUMN 14,	LINE 65,	change "wherein each spacer is upon the oxide layer, is" to --the oxide--
CLAIM 22,	COLUMN 14,	LINE 66,	change "both the polysilicon layer and" to --lateral edges of--
CLAIM 22,	COLUMN 14,	LINE 67,	change "layer, and is adjacent to an area of the plurality of areas;" to --material;--
CLAIM 22,	COLUMN 15,	LINE 1,	change "forming" to --removing a portion of material from the plurality of exposed areas of the oxide at locations between adjacent portions of the plurality of spacers to form-- and delete "below"
CLAIM 22,	COLUMN 15,	LINE 2,	delete "the oxide layer and from top edges"
CLAIM 22,	COLUMN 15,	LINES 3-6,	change "substrate, wherein each isolation trench of the plurality of isolation trenches is adjacent to and below a pair of the spacers and is situated at a corresponding area of the plurality of areas;" to --substrate;--
CLAIM 22,	COLUMN 15,	LINES 7-8,	change "rounding the top edges of each isolation trench of the plurality of isolation trenches;" to --implanting ions in the plurality of isolation trenches in a direction substantially orthogonal to a plane of the oxide;--

In the claims (continued):

CLAIM 22,	COLUMN 15,	LINES 9-10,	change "filling each isolation trench of the plurality of isolation trenches with" to --depositing-- and change "layer," to --material filling each isolation trench,--
CLAIM 22,	COLUMN 15,	LINE 11,	change "third layer" to --third material-- and change "above the oxide layer" to --over remaining portions of the oxide--
CLAIM 22,	COLUMN 15,	LINE 12,	delete "filling"
CLAIM 22,	COLUMN 15,	LINE 13,	delete "is performed by depositing the conformal third layer,"
CLAIM 22,	COLUMN 15,	LINE 14,	delete "and"
CLAIM 22,	COLUMN 15,	LINE 16,	change "dielectric layer" to --dielectric material--
CLAIM 22,	COLUMN 15,	LINE 17,	change "third layer;" to --third material;--
CLAIM 22,	COLUMN 15,	LINE 18,	delete "substantially simultaneously subjecting an entire upper"
CLAIM 22,	COLUMN 15,	LINE 19,	change "surface contour" to --removing portions-- and change "third layer to a" to --third material by--
CLAIM 22,	COLUMN 15,	LINE 20,	delete "process and planarizing"
CLAIM 22,	COLUMN 15,	LINE 21,	change "layer" to --material-- and delete "therefrom"
CLAIM 22,	COLUMN 15,	LINES 23-24,	insert a paragraph break after "and" and then change "fusing the oxide layer, spacers and conformal third layer;" to --removing the first dielectric material, polysilicon and portions of the oxide underlying the first dielectric material such that the conformal third material fills each isolation trench, extends horizontally away from each isolation trench upon remaining portions of the oxide and sidewalls of the conformal third material extend from an upper surface of the semiconductor substrate to the upper surface contour of the conformal third material and the sidewalls are oriented substantially orthogonal to the upper surface contour of the conformal third material;--
CLAIM 22,	COLUMN 15,	LINE 25,	change "third layer is an" to --third material is--
CLAIM 22,	COLUMN 15,	LINE 26,	change "material that" to --and--
CLAIM 22,	COLUMN 15,	LINE 30,	change "third layer," to --third material,--
CLA1M 22,	COLUMN 15,	LINE 31,	change "layer; and" to --material; and--
CLAIM 22,	COLUMN 15,	LINE 33,	change "third layer," to --third material,--
CLAIM 23,	COLUMN 15,	LINE 37,	change "oxide layer" to --oxide--
CLAIM 23,	COLUMN 15,	LINE 38,	change "polysilicon layer" to --first polysilicon material-- and change "oxide layer;" to --oxide;--
CLAIM 23,	COLUMN 15,	LINE 39,	change "dielectric layer" to --dielectric material-- and change "polysilicon layer;" to --first polysilicon material;--
CLA1M 23,	COLUMN 15,	LINE 40,	change "dielectric layer" to --dielectric material-- and after "and the" insert --first--
CLAIM 23,	COLUMN 15,	LINES 41-42,	change "layer to expose the oxide layer at a plurality of areas;" to --material to expose a plurality of areas of the oxide;--

In the claims (continued):

CLAIM 23,	COLUMN 15,	LINE 43,	change "dielectric layer conformally" to --dielectric material--
CLAIM 23,	COLUMN 15,	LINE 44,	delete "oxide layer, the polysilicon layer, and the"
CLAIM 23,	COLUMN 15,	LINE 45,	delete "layer, wherein the forming a second dielectric layer"
CLAIM 23,	COLUMN 15,	LINE 46,	change "includes forming a second dielectric layer on" to --material--
CLAIM 23,	COLUMN 15,	LINES 47-48,	after "with the" insert --plurality of-- and change "oxide layer at the plurality of areas;" to --areas of the oxide;--
CLAIM 23,	COLUMN 15,	LINE 49,	change "dielectric layer" to --dielectric material--
CLAIM 23,	COLUMN 15,	LINE 50,	change "from the second dielectric layer," to --at peripheral edges of the plurality of exposed areas of--
CLAIM 23,	COLUMN 15,	LINE 51,	delete "wherein each spacer of the plurality of spacers is upon"
CLAIM 23,	COLUMN 15,	LINE 52,	change "oxide layer, is" to --oxide in-- and change "both the polysilicon" to --lateral edges of--
CLAIM 23,	COLUMN 15,	LINES 53-54,	delete "layer and" and change "dielectric layer, and is adjacent to an area of the plurality of areas;" to --dielectric material;--
CLAIM 23,	COLUMN 15,	LINE 55,	change "forming" to --removing a portion of material from the plurality of exposed areas of the oxide at locations between adjacent portions of the plurality of spacers to form-- and delete "below"
CLAIM 23,	COLUMN 15,	LINE 56,	delete "the oxide layer and from top edges"
CLAIM 23,	COLUMN 15,	LINES 57-60,	change "substrate, wherein each isolation trench of the plurality of isolation trenches is adjacent to and below a pair of the spacers and is situated at a corresponding area of the plurality of areas;" to --substrate;--
CLAIM 23,	COLUMN 15,	LINE 62,	before "filling" insert --implanting ions in the plurality of isolation trenches in a direction substantially orthogonal to a plane of the oxide;--, insert a paragraph break, and then insert --depositing a conformal third material-- and change "trench with a conformal third layer," to --trench,--
CLAIM 23,	COLUMN 15,	LINE 63,	change "third layer extending above" to --third material extending over remaining portions of--
CLAIM 23,	COLUMN 15,	LINE 64,	delete "layer"
CLAIM 23,	COLUMN 15,	LINE 65,	delete "filling is performed by depositing the conformal"
CLAIM 23,	COLUMN 15,	LINE 66,	delete "third layer, and"
CLAIM 23,	COLUMN 16,	LINE 1,	change "dielectric layer" to --dielectric material--
CLAIM 23,	COLUMN 16,	LINE 2,	change "third layer;" to --third material;--
CLAIM 23,	COLUMN 16,	LINE 3,	delete "substantially simultaneously subjecting an entire upper"

In the claims (continued):

CLAIM 23,	COLUMN 16,	LINE 4,	change "surface contour" to --removing portions-- and change "third layer to a" to --third material overlying the remaining portions of the oxide by--
CLAIM 23,	COLUMN 16,	LINE 5,	delete "process and planarizing"
CLAIM 23,	COLUMN 16,	LINE 6,	change "layer" to --material-- and delete "therefrom"
CLAIM 23,	COLUMN 16,	LINE 8,	change "oxide layer" to --oxide--
CLAIM 23,	COLUMN 16,	LINE 10,	change "oxide layer" to --oxide--
CLAIM 23,	COLUMN 16,	LINE 13,	change "layer composed of" to --second--
CLAIM 23,	COLUMN 16,	LINE 14,	after "polysilicon" insert --material-- and delete "layer"
CLAIM 23,	COLUMN 16,	LINE 16,	change "third layer," to --conformal third material,--
CLAIM 23,	COLUMN 16,	LINE 17,	change "layer composed of polysilicon" to --second polysilicon material--
CLAIM 23,	COLUMN 16,	LINE 19,	change "fusing the oxide layer, spacers and conformal third layer;" to --removing the first dielectric material, first polysilicon material and portions of the oxide underlying the first dielectric material such that the conformal third material fills each isolation trench, extends horizontally away from each isolation trench upon remaining portions of the oxide and sidewalls of the conformal third material originate on an upper surface of the semiconductor substrate and extend to the upper surface contour of the conformal third material, the sidewalls are oriented substantially orthogonal to the upper surface contour of the conformal third material;--
CLAIM 24,	COLUMN 16,	LINE 25,	delete "forming an oxide layer upon a semiconductor substrate;"
CLAIM 24,	COLUMN 16,	LINE 26,	change "a polysilicon layer" to --polysilicon-- and change "the oxide layer;" to --an oxide overlying a semiconductor substrate;--
CLAIM 24,	COLUMN 16,	LINE 27,	change "dielectric layer" to --dielectric material-- and change "polysilicon layer;" to --polysilicon;--
CLAIM 24,	COLUMN 16,	LINE 28,	change "dielectric layer" to --dielectric material--
CLAIM 24,	COLUMN 16,	LINE 29,	change "layer to expose the oxide layer at a plurality of" to --to expose a plurality of areas of the oxide;--
CLAIM 24,	COLUMN 16,	LINE 30,	delete "areas;"
CLAIM 24,	COLUMN 16,	LINE 31,	change "dielectric layer conformally" to --dielectric material--
CLAIM 24,	COLUMN 16,	LINE 32,	change "oxide layer, the polysilicon layer," to --polysilicon,--
CLAIM 24,	COLUMN 16,	LINE 33,	change "layer, wherein the forming a second dielectric layer" to --material--
CLAIM 24,	COLUMN 16,	LINE 34,	delete "includes forming a second dielectric layer on"
CLAIM 24,	COLUMN 16,	LINE 35,	after "with the" insert --plurality of-- and change "oxide layer at the plurality of" to --areas of the oxide;--
CLAIM 24,	COLUMN 16,	LINE 36,	delete "areas;"

In the claims (continued):

CLAIM 24,	COLUMN 16,	LINE 37,	change "dielectric layer" to --dielectric material--
CLAIM 24,	COLUMN 16,	LINE 38,	change "from the second dielectric layer," to --at peripheral edges of the plurality of exposed areas of--
CLAIM 24,	COLUMN 16,	LINE 39,	delete "wherein each spacer of the plurality of spacers is upon"
CLAIM 24,	COLUMN 16,	LINE 40,	delete "layer, is" and change "both the polysilicon" to --lateral edges of--
CLAIM 24,	COLUMN 16,	LINE 41,	delete "layer and" and change "layer, and is adjacent to an" to --material;--
CLAIM 24,	COLUMN 16,	LINE 42,	delete "area of the plurality of areas;"
CLAIM 24,	COLUMN 16,	LINE 43,	change "forming" to --removing material from the plurality of exposed areas of the oxide at locations between adjacent portions of the plurality of spacers to form-- and delete "below"
CLAIM 24,	COLUMN 16,	LINE 44,	delete "the oxide layer and from top edges"
CLAIM 24,	COLUMN 16,	LINES 45-48,	change "substrate, wherein each isolation trench of the plurality of isolation trenches is adjacent to and below a pair of the spacers and is situated at a corresponding area of the plurality of areas;" to --substrate;--
CLAIM 24,	COLUMN 16,	LINE 50,	after "trenches;" insert a paragraph break and then insert --implanting ions in the plurality of isolation trenches in a direction substantially orthogonal to a plane of the oxide;--
CLAIM 24,	COLUMN 16,	LINE 51,	before "filling" insert --depositing a conformal third material-- and change "trench with a conformal third layer," to --trench,--
CLAIM 24,	COLUMN 16,	LINE 52,	change "third layer extending above" to --third material extending over remaining portions of--
CLAIM 24,	COLUMN 16,	LINE 53,	change "layer in" to --in--
CLAIM 24,	COLUMN 16,	LINE 54,	delete "filling is performed by depositing the conformal"
CLAIM 24,	COLUMN 16,	LINE 55,	delete "third layer, and"
CLAIM 24,	COLUMN 16,	LINE 57,	change "dielectric layer" to --dielectric material--
CLAIM 24,	COLUMN 16,	LINE 58,	change "third layer;" to --third material;--
CLAIM 24,	COLUMN 16,	LINE 59,	delete "substantially simultaneously subjecting an entire upper"
CLAIM 24,	COLUMN 16,	LINE 60,	change "surface contour" to --removing portions--and change "layer to a" to --material overlying the remaining portions of the oxide by--
CLAIM 24,	COLUMN 16,	LINE 61,	change "process comprising" to --the conformal third material to form therefrom an upper surface for each isolation trench that is co-planar to the other upper surfaces using--
CLAIM 24,	COLUMN 16,	LINE 62,	change "third layer" to --third material--
CLAIM 24,	COLUMN 16,	LINE 63,	change "dielectric" to --dielectric material-- and change "range from" to --range of from--

In the claims (continued):

CLAIM 24,	COLUMN 16,	LINES 64-66,	change "2:1 and planarizing the conformal third layer to form therefrom an upper surface for each isolation trench that is co-planar to the other upper surfaces; and" to --2:1;--
CLAIM 24,	COLUMN 16,	LINE 67,	change "fusing the oxide layer," to --heat treating the oxide,-- change "third layer;" to --third material to fuse the oxide, spacers and conformal third material; and--, insert a paragraph break and then insert --removing the first dielectric material, polysilicon, and portions of the oxide underlying the first dielectric material such that the conformal third material fills each isolation trench, extends horizontally away from each isolation trench upon remaining portions of the oxide and sidewalls of the conformal third material originate on an upper surface of the semiconductor substrate to the upper surface contour of the conformal third material and the sidewalls are substantially orthogonal to the upper surface contour of the conformal third material;--
CLAIM 24,	COLUMN 17,	LINE 5,	change "third layer," to --third material,--
CLAIM 24,	COLUMN 17,	LINES 6-11,	delete "corresponding pair of the spacers, wherein depositing is carried out to the extent of filling each isolation trench and extending over the spacers and over the first dielectric material so as to define an upper surface contour of the conformal third material;"
CLAIM 26,	COLUMN 17,	LINE 16,	change "oxide layer" to --oxide--
CLAIM 26,	COLUMN 17,	LINE 17,	change "polysilicon layer" to --first polysilicon material-- and change "oxide layer;" to --oxide;--
CLAIM 26,	COLUMN 17,	LINE 18,	change "a silicon nitride layer" to --silicon nitride-- and change "polysilicon layer;" to --first polysilicon material;--
CLAIM 26,	COLUMN 17,	LINE 19,	change "layer and the" to --and the first--
CLAIM 26,	COLUMN 17,	LINE 20,	change "layer to expose" to --material to expose a plurality of areas of-- and change "layer at a plurality" to --material;--
CLAIM 26,	COLUMN 17,	LINE 21,	delete "of areas;"
CLAIM 26,	COLUMN 17,	LINE 22,	change "layer over the pad oxide" to --material over--
CLAIM 26,	COLUMN 17,	LINES 23-25,	delete "layer and over" and delete "layer, wherein the forming a first silicon dioxide layer includes forming a first silicon dioxide layer on"
CLAIM 26,	COLUMN 17,	LINE 26,	delete "layer" and change "areas;" to --exposed areas of the pad oxide;--
CLAIM 26,	COLUMN 17,	LINE 27,	change "dioxide layer" to --dioxide material--
CLAIM 26,	COLUMN 17,	LINES 28-29,	change "from the first silicon dioxide layer, wherein each spacer of the plurality of spacers is situated" to --at peripheral edges of the plurality of exposed areas of--

In the claims (continued):

CLAIM 26,	COLUMN 17,	LINE 30,	delete “upon,” delete “layer, is” and after “with” insert --lateral edges of--
CLAIM 26,	COLUMN 17,	LINE 31,	change “nitride layer and the polysilicon layer, and is adjacent to” to --nitride and the first polysilicon material;--
CLAIM 26,	COLUMN 17,	LINE 32,	delete “an area of the plurality of areas;”
CLAIM 26,	COLUMN 17,	LINE 33,	change “forming” to --removing a portion of material from the plurality of exposed areas at locations between adjacent portions of the plurality of spacers to form-- and delete “below”
CLAIM 26,	COLUMN 17,	LINE 34,	delete “the pad oxide layer and from top edges”
CLAIM 26,	COLUMN 17,	LINE 41,	change “substrate;” to --substrate by implanting ions in the plurality of isolation trenches in a direction substantially orthogonal to a plane of the pad oxide;--
CLAIM 26,	COLUMN 17,	LINE 44,	delete “layer”
CLAIM 26,	COLUMN 17,	LINE 47,	before “filling” insert --depositing a conformal second material-- and delete “with a conformal second layer,”
CLAIM 26,	COLUMN 17,	LINE 48,	change “layer extending above” to --material extending over remaining portions of--
CLAIM 26,	COLUMN 17,	LINE 49,	delete “layer”
CLAIM 26,	COLUMN 17,	LINE 50,	delete “filling is performed by depositing the”
CLAIM 26,	COLUMN 17,	LINE 51,	delete “conformal second layer, and”
CLAIM 26,	COLUMN 17,	LINE 53,	delete “layer”
CLAIM 26,	COLUMN 17,	LINE 55,	change “layer;” to --material;--
CLAIM 26,	COLUMN 17,	LINE 56,	delete “substantially simultaneously subjecting an entire upper”
CLAIM 26,	COLUMN 17,	LINE 57,	change “surface contour” to --removing a portion-- and change “layer to a” to --material by--
CLAIM 26,	COLUMN 17,	LINE 58,	delete “process and planarizing”
CLAIM 26,	COLUMN 17,	LINE 59,	change “layer” to --material-- and delete “therefrom”
CLAIM 26,	COLUMN 17,	LINES 61-62,	change “pad oxide layer; and” to --pad oxide;--
CLAIM 26,	COLUMN 17,	LINE 63,	change “fusing” to --heat treating the pad oxide, liner, spacers and conformal second material to fuse-- and change “oxide layer,” to --oxide,--
CLAIM 26,	COLUMN 17,	LINE 64,	change “second layer;” to --second material; and--, insert a paragraph break, and then insert --removing the silicon nitride, first polysilicon material and portions of the pad oxide underlying the silicon nitride such that the conformal second material fills each isolation trench, extends horizontally away from each isolation trench upon remaining portions of the pad oxide and sidewalls of the conformal second material originate on an upper surface of the semiconductor substrate and continue to the upper surface contour of the conformal second material, the sidewalls lie substantially orthogonal to the upper surface contour of the conformal second material;--

In the claims (continued):

CLAIM 29,	COLUMN 18,	LINES 9-10,	delete "exposing the pad layer upon a portion of a surface of the semiconductor substrate;"
CLAIM 29,	COLUMN 18,	LINE 11,	change "layer upon the" to --upon a--
CLAIM 29,	COLUMN 18,	LINE 14,	change "a layer composed of" to --a second--
CLAIM 29,	COLUMN 18,	LINE 15,	after "polysilicon" insert --material-- and delete "layer"
CLAIM 29,	COLUMN 18,	LINE 16,	change "spacers," to --spacers;--
CLAIM 29,	COLUMN 18,	LINE 17,	change "layer composed of polysilicon" to --second polysilicon material--
CLAIM 30,	COLUMN 18,	LINES 21-22,	delete "providing a semiconductor substrate having a top surface with an oxide layer thereon;"
CLAIM 30,	COLUMN 18,	LINE 23,	change "a polysilicon layer upon the oxide layer;" to --polysilicon upon an oxide overlying a semiconductor substrate;--
CLAIM 30,	COLUMN 18,	LINE 24,	change "first layer" to --first material-- and change "polysilicon layer;" to --polysilicon;--
CLAIM 30,	COLUMN 18,	LINE 25,	change "first layer" to --first material--
CLAIM 30,	COLUMN 18,	LINE 26,	change "layer to expose the oxide layer at a plurality of areas;" to --to expose a plurality of areas of the oxide;--
CLAIM 30,	COLUMN 18,	LINE 28,	change "layer at the plurality of areas," to --at the plurality of areas;--, insert a paragraph break, then insert --implanting ions in the plurality of isolation trenches in a direction substantially orthogonal to a plane of the oxide;-- and then insert another paragraph break
CLAIM 30,	COLUMN 18,	LINE 33,	change "oxide layer" to --oxide-- and change "first layer" to --first material--
CLAIM 30,	COLUMN 18,	LINE 34,	change "polysilicon layer;" to --polysilicon;--
CLAIM 30,	COLUMN 18,	LINE 37,	change "layer into" to --into --
CLAIM 30,	COLUMN 18,	LINE 39,	change "second layer" to --second material--
CLAIM 30,	COLUMN 18,	LINE 40,	change "oxide layer" to --oxide--
CLAIM 30,	COLUMN 18,	LINE 42,	change "second layer," to --second material,--
CLAIM 30,	COLUMN 18,	LINE 44,	change "first layer" to --first material--
CLAIM 30,	COLUMN 18,	LINE 45,	change "second layer;" to --second material;--
CLAIM 30,	COLUMN 18,	LINE 47,	change "layer and" to --material and--
CLAIM 30,	COLUMN 18,	LINE 48,	change "oxide layer," to --oxide,--
CLAIM 30,	COLUMN 18,	LINE 51,	change "second layer" to --second material--
CLAIM 30,	COLUMN 18,	LINE 53,	change "fusing the oxide layer, spacer and second layer;" to --removing the first material, polysilicon and portions of the oxide underlying the first material such that the second material fills each isolation trench, extends horizontally away from each isolation trench upon remaining portions of the oxide and sidewalls of the second material initiate on an upper surface of the semiconductor substrate and end at the upper surface contour of the second material, the sidewalls are substantially orthogonal to the upper surface contour of the second material;--

In the claims (continued):

CLAIM 30,	COLUMN 18,	LINE 55,	change "second layer," to --second material,--
CLAIM 31,	COLUMN 18,	LINE 57,	change "as defined in" to --according to--
CLAIM 31,	COLUMN 18,	LINE 60,	before "doping" insert a paragraph break and then insert --wherein implanting ions in the plurality of isolation trenches in a direction substantially orthogonal to a plane of the oxide further comprises:--
CLAIM 33,	COLUMN 19,	LINES 5-6,	delete "providing a semiconductor substrate having a top surface with an oxide layer thereon;"
CLAIM 33,	COLUMN 19,	LINE 7,	change "layer upon the oxide layer;" to --material upon an oxide overlying a semiconductor substrate;--
CLAIM 33,	COLUMN 19,	LINE 8,	change "layer to expose the oxide" to --material to expose a plurality of areas of the oxide;--
CLAIM 33,	COLUMN 19,	LINE 9,	delete "layer at a plurality of areas;"
CLAIM 33,	COLUMN 19,	LINE 11,	delete "layer"
CLAIM 33,	COLUMN 19,	LINE 16,	change "oxide layer" to --oxide-- and change "first layer;" to --first material;--
CLAIM 33,	COLUMN 19,	LINE 19,	delete "layer"
CLAIM 33,	COLUMN 19,	LINE 21,	change "second layer" to --second material--
CLAIM 33,	COLUMN 19,	LINE 22,	change "oxide layer" to --oxide--
CLAIM 33,	COLUMN 19,	LINE 24,	change "second layer," to --second material,--
CLAIM 33,	COLUMN 19,	LINE 26,	change "first layer" to --first material--
CLAIM33,	COLUMN 19,	LINE 27,	change "second layer;" to --second material;--
CLAIM 33,	COLUMN 19,	LINE 29,	change "layer" to --material--
CLAIM 33,	COLUMN 19,	LINE 30,	change "oxide layer," to --oxide,--
CLAIM 33,	COLUMN 19,	LINE 31,	delete "substantially simultaneously subjecting an"
CLAIM 33,	COLUMN 19,	LINE 32,	change "entire upper surface contour" to --removing portions-- and change "layer to a" to --material by--
CLAIM 33,	COLUMN 19,	LINE 33,	change "process; and" to --the entire upper surface contour of the second material;--
CLAIM 33,	COLUMN 19,	LINES 34-35,	change "fusing the oxide layer, electrically insulative material, spacer and second layer;" to --implanting ions in the plurality of isolation trenches in a direction substantially orthogonal to a plane of the oxide; and--, insert a paragraph break and then insert --removing the first material and portions of the oxide underlying the first material such that the second material fills each isolation trench, extends horizontally away from each isolation trench upon remaining portions of the oxide and sidewalls of the second material commence at an upper surface of the semiconductor substrate and end at the upper surface contour of the second material and the sidewalls are oriented substantially orthogonal to the upper surface contour of the second material;--
CLAIM 33,	COLUMN 19,	LINE 37,	change "second layer," to --second material,--
CLAIM 34,	COLUMN 19,	LINE 41,	change "type;" to --type; and--
CLAIM 34,	COLUMN 19,	LINE 42,	delete "and"

In the claims (continued):

CLAIM 36,	COLUMN 19,	LINES 57-58,	delete "providing a semiconductor substrate having a top surface with an oxide layer thereon;"
CLAIM 36,	COLUMN 19,	LINE 59,	change "a polysilicon layer upon the oxide layer;" to --polysilicon upon an oxide overlying a semiconductor substrate;--
CLAIM 36,	COLUMN 19,	LINE 60,	change "first layer" to --first material-- and change "polysilicon layer;" to --polysilicon;--
CLAIM 36,	COLUMN 19,	LINE 63,	change "oxide layer" to --oxide-- and change "first layer" to --first material--
CLAIM 36,	COLUMN 19,	LINE 64,	change "polysilicon layer;" to --polysilicon;--
CLAIM 36,	COLUMN 19,	LINE 65,	delete "from an opening thereto"
CLAIM 36,	COLUMN 19,	LINE 66,	delete "at top edges at the top surface of the semiconductor"
CLAIM 36,	COLUMN 19,	LINE 67,	delete "substrate and below the oxide layer"
CLAIM 36,	COLUMN 20,	LINE 7,	change "oxide layer" to --oxide-- and change "first layer" to --first material--
CLAIM 36,	COLUMN 20,	LINE 8,	change "polysilicon layer," to --polysilicon,--
CLAIM 36,	COLUMN 20,	LINE 13,	change "oxide layer" to --oxide-- and change "first layer" to --first material--
CLAIM 36,	COLUMN 20,	LINE 14,	change "polysilicon layer;" to --polysilicon;--
CLA1M 36,	COLUMN 20,	LINE 15,	delete "from an opening thereto"
CLAIM 36,	COLUMN 20,	LINE 16,	delete "at top edges at the top surface of the semiconductor"
CLAIM 36,	COLUMN 20,	LINE 17,	delete "substrate and below the oxide layer"
CLAIM 36,	COLUMN 20,	LINE 26,	change "oxide layer" to --oxide-- and change "first layer" to --first material--
CLAIM 36,	COLUMN 20,	LINE 27,	change "polysilicon layer," to --polysilicon,--
CLAIM 36,	COLUMN 20,	LINE 32,	before "forming" insert --doping the first isolation trench and second isolation trench by implanting ions in a direction substantially orthogonal to a plane of the oxide;-- and then insert a paragraph break
CLAIM 36,	COLUMN 20,	LINE 35,	change "forming" to --depositing-- and change "layer, composed of" to --material comprising--
CLAIM 36,	COLUMN 20,	LINE 36,	before "filling" insert --the conformal second material--
CLAIM 36,	COLUMN 20,	LINES 37-38,	change "therebetween and above" to --over remaining portions of-- and delete "layer"
CLAIM 36,	COLUMN 20,	LINE 40,	delete "filling is performed by"
CLAIM 36,	COLUMN 20,	LINE 41,	delete "depositing the conformal second layer, and"
CLAIM 36,	COLUMN 20,	LINE 44,	change "layer" to --material--
CLAIM 36,	COLUMN 20,	LINE 45,	change "layer;" to --material;--
CLAIM 36,	COLUMN 20,	LINE 46,	change "substantially simultaneously subjecting an entire" to --planarizing portions of the--
CLAIM 36,	COLUMN 20,	LINE 47,	change "second layer to a planarizing" to --conformal second material;--
CLAIM 36,	COLUMN 20,	LINE 48,	delete "process;"
CLAIM 36,	COLUMN 20,	LINE 50,	change "layer" to --material--
CLAIM 36,	COLUMN 20,	LINE 52,	change "oxide layer; and" to --oxide;--

In the claims (continued):

CLAIM 36,	COLUMN 20,	LINE 53,	change "fusing" to --heat treating the oxide, first spacer, second spacer and conformal second material of the first isolation structure to fuse the oxide, first spacer, second spacer and conformal second material of the first isolation structure;--, then insert a paragraph break and then change "the oxide layer," to --heat treating the oxide, first spacer, second spacer and conformal second material of the second isolation structure to fuse the oxide,--
CLAIM 36,	COLUMN 20,	LINE 54,	change "second layer of the first isolation structure and" to --second material--
CLAIM 36,	COLUMN 20,	LINE 55,	delete "fusing the oxide layer, first spacer, second spacer and"
CLAIM 36,	COLUMN 20,	LINE 56,	delete "conformal second layer" and change "structure;" to --structure; and--, insert a paragraph break and then insert --removing the first material, polysilicon and portions of the oxide underlying the first material such that the conformal second material fills each isolation trench, extends horizontally away from each isolation trench upon remaining portions of the oxide and sidewalls of the second material initiate on an upper surface of the semiconductor substrate and extend toward the upper surface contour of the second material, the sidewalls are oriented substantially orthogonal to the upper surface contour of the second material;--
CLAIM 36,	COLUMN 20,	LINE 58,	change "layer," to --material,--
CLAIM 37,	COLUMN 20,	LINES 62-63,	delete "providing a semiconductor substrate having a top surface with an oxide layer thereon;"
CLAIM 37,	COLUMN 20,	LINE 64,	change "layer upon the oxide layer;" to --material upon an oxide overlying a semiconductor substrate;--
CLAIM 37,	COLUMN 20,	LINE 67,	change "oxide layer" to --oxide-- and change "first layer;" to --first material;--
CLAIM 37,	COLUMN 21,	LINE 1,	delete "from an opening thereto"
CLAIM 37,	COLUMN 21,	LINE 2,	delete "at the top surface of the semiconductor substrate and"
CLAIM 37,	COLUMN 21,	LINE 3,	delete "below the oxide layer"
CLAIM 37,	COLUMN 21,	LINE 9,	change "oxide layer" to --oxide-- and change "first layer," to --first material,--
CLAIM 37,	COLUMN 21,	LINE 15,	change "oxide layer" to --oxide-- and change "first layer;" to --first material;--
CLAIM 37,	COLUMN 21,	LINE 16,	delete "below the oxide layer"

In the claims (continued):

CLAIM 37,	COLUMN 21,	LINE 26,	change “oxide layer” to --oxide-- and change “first layer,” to --first material,--
CLAIM 37,	COLUMN 22,	LINE 1,	before “forming” insert --doping the first isolation trench and second isolation trench by implanting ions in a direction substantially orthogonal to a plane of the oxide;-- and then insert a paragraph break
CLAIM 37,	COLUMN 22,	LINE 4,	change “forming” to --depositing-- and change “layer composed of” to --material comprising--
CLAIM 37,	COLUMN 22,	LINE 5,	change “material, conformally filling” to --material to fill--
CLAIM 37,	COLUMN 22,	LINE 7,	change “therebetween and above the oxide layer” to --over remaining portions of the oxide--
CLAIM 37,	COLUMN 22,	LINE 9,	delete “filling is performed”
CLAIM 37,	COLUMN 22,	LINE 10,	change “by depositing the conformal second layer, and” to --the--
CLAIM 37,	COLUMN 22,	LINE 13,	change “first layer” to --first material--
CLAIM 37,	COLUMN 22,	LINE 14,	change “second layer;” to --second material;--
CLAIM 37,	COLUMN 22,	LINE 15,	delete “substantially simultaneously subjecting an entire upper”
CLAIM 37,	COLUMN 22,	LINE 16,	delete “surface contour of the second layer to a planarizing”
CLAIM 37,	COLUMN 22,	LINE 17,	delete “process and” and change “layer” to --material--
CLAIM 37,	COLUMN 22,	LINES 19-25,	change “planar upper surface from the conformal the conformal second layer and the first and second spacers of the respective first and second isolation structures, and being situated above the oxide layer, wherein the microelectronic structure is defined at least in part by the active area, the conformal second layer, and the first and second isolation trenches; and” to --planar upper surface;--
CLAIM 37,	COLUMN 22,	LINES 26-29,	change “fusing the oxide layer, first spacer, second spacer and conformal second layer of the first isolation structure and fusing the oxide layer, first spacer, second spacer and conformal second layer of the second isolation structure.” to --heat treating the oxide, first spacer, second spacer and conformal second material of the first isolation structure to fuse the oxide, first spacer, second spacer and conformal second material of the first isolation structure;-- --heat treating the oxide, first spacer, second spacer and conformal second material of the second isolation structure to fuse the oxide, first spacer, second spacer and conformal second material of the second isolation structure; and--

In the claims (continued):

--removing the first material and portions of the oxide underlying the first material such that the conformal second material fills each isolation trench, extends horizontally away from each isolation trench upon remaining portions of the oxide and sidewalls of the conformal second material originate on an upper surface of the semiconductor substrate and extend toward the upper surface contour of the conformal second material, the sidewalls are oriented substantially orthogonal to the upper surface contour of the conformal second material.--